

FORM PTO-1449 US Dept. of Commerce Patent and Trademark Office INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)	ATTORNEY DOCKET NO.	SERIAL NO.
	ATMI-272	09/093,291
	APPLICANT Peter C. Van Buskirk, et al.	
	FILING DATE June 8, 1998	GROUP 1763 1746

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	08/975,366		Van Buskirk and Kirlin			11/20/98

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	NO

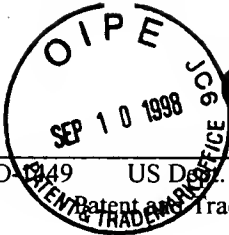
OTHER DOCUMENTS (Including Author, Title, Journal-Date, Page Number, Etc.)

AB	Koteki, D.E., "A Review of High Dielectric Materials for DRAM Capacitors", <i>Integ. Ferro.</i> , 1997, Vol. 16, pp. 1-19.
AC	Jeon, et al., "Thermal Stability of Ir/Polycrystalline-Si Structure for Bottom Electrode of Integrated Ferroelectric Capacitors", <i>Appl. Physics Lett.</i> , 1997, Vol. 71(4), pp. 467-469.
AD	Williams, et al., "Etch Rates for Micromachining Processing", <i>Journ. For Microelectromechanical Systems</i> , December 1996, Vol. 5 (4), pp. 256-269
AE	Vugts, et al., "Si/XeF ₂ Etching-Temperature Dependence", 1996, <i>J. Vac. Sci. Tech. A</i> , Vol. 14(5), pp. 2766-2774
AF	P.C. Fazan, et al., "Stacked Capacitor Modules for 64 Mb DRAMs and Beyond", <i>Semiconductor Inter.</i> , 1992, Vol. 108, pp. 108-112
AG	L. H. Parker, et al., "Ferroelectric Materials for 64Mb and 256Mb DRAMs", <i>IEEE Circuits and Devices Mag.</i> , Jan. 1990, pp. 17-26

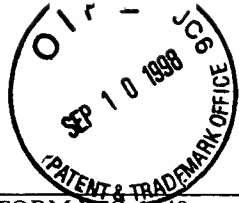
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two	AH	R. E. Sievers, et al., "Volatile Barium B-Diketonates for Use as MOCVD Precursors", <i>Coord. Chem. Rev.</i> , 1993, pp. 285-291.					
two	AI	C. Farrell, et al., "A Reactive Ion Etch Study for Producing Patterned Platinum Structures", Presented at ISIF 96, March 18,19,20, 1996 Tempe AZ. (to be published in Integrated Ferroelectrics).					
two	AJ	K. R. Milkove and C. X. Wang, "Insight into the dry cleaning of Fence Patterned Platinum Structures", <i>J. Vac. Sci. Tech. A</i> , 1997, Vol. 15(3), pp. 596-603					
two	AK	Chang, F.I., et al., "Gas Phase Silicon Micromachining with Xenon Difluoride", <i>Proc of SPIE</i> , 1995, Vol. 2641, pp. 117-128.					
two	AL	Bensaola, A. et al., "Low Temperature Ion Beam Enhanced Etching of Tungsten Films with Xenon Difluoride", <i>Appl. Phys. Lett.</i> , Dec. 1986, Vol. 49(24), pp. 1663-1664					
two	AM	G. Stauf, "BaSrTiO3 Etching for Advanced Microelectronic Devices", U.S. Army Missile Command, Report Number, DAAH01-96-C-R035, 1/10/96-1/30/98.					
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	AN	Ebsworth, E.A.V., et al., "Formation of Iridium Fluoroacyl Complexes by Reaction of Iridium Carbonyls with Xenon Difluoride and Reactions of these to Generate Unusual Acyl Complexes", <i>J. Chem. Soc., Dalton Trans.</i> , 1993, ISS. 7, pp. 1031-7					
	AO	Blake, A.J., et al., "Novel Reaction of an Iridium Carbonyl Complex with Xenon Difluoride: The First Metal Fluoroacyl Complex", <i>J. Chem. Soc., Chem. Commun.</i> , 1988, ISS.8, pp. 529-530					
	AP	Sladkey, F.O., et al., "Xenon Difluoride as a Fluoride Ion Donor" <i>J. Chem. Soc. A</i> , 1969, Vol. 14, pp. 2179-88					
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EXAMINER <i>W. C. Olson</i>					DATE CONSIDERED 9/29/89		
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